*			Atty. Docket No.	Serial N	Vo.:	.g <b>■</b>
Form PTO-1449 (Rev. 2-32)	U.S. Department Patent & Trader		Q61222	Confirm	nation No.:	8. P. 3586 
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)			Applicant: Toshiro HAYAKAWA			
			Filing Date: February 09, 2001	Group:		309
		U.S. PATI	ENT DOCUMENTS	· · · · · · · · · · · · · · · · · · ·		
Examiner Initial	Document Number	er Date	Name	Class	Sub- Class	Filing Date (if appropriate)
CB+/CM	5,461,637	10/24/95	MOORADIAN et al	372	92	
CBOYCHN	5,627,853	05/06/97	MOORADIAN e tal	372	92	
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		FOREIGN PA	TENT DOCUMENTS			·· -
	Document	FOREIGN PA	Country	Class	Sub- class	Translation Yes/No
	Document			Class	1	
	Document			Class	1	
	Document			Class	1	
	Document			Class	1	
	Document			Class	1	
	Document			Class	1	
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		Date	Country		class	
	OTHER DOCU	Date  MENTS (Including	Country  g Author, Title, Date, Pert	inent Page	class	Yes/No
OBH CHI	OTHER DOCU  Shuji Nakamura et a Fundamental Trans	JMENTS (Includinal, "InGaN/GaN/Awerse Mode", Septe	Country  g Author, Title, Date, Pert GaN-Based Laser Diodes ember 15, 1998, Jpn. J. Ap	inent Page: Grown on pl. Phys. V	s, Etc.) GaN Substra	Yes/No  actes with a 1) L1020-L1022
UBA CHI	OTHER DOCU  Shuji Nakamura et a Fundamental Trans	JMENTS (Includinal, "InGaN/GaN/Awerse Mode", Septe	Country  g Author, Title, Date, Pert	inent Page: Grown on pl. Phys. V	s, Etc.) GaN Substra	Yes/No  actes with a 1) L1020-L1022
	OTHER DOCU  Shuji Nakamura et a Fundamental Trans	JMENTS (Includinal, "InGaN/GaN/Awerse Mode", Septe	Country  g Author, Title, Date, Pert GaN-Based Laser Diodes ember 15, 1998, Jpn. J. Ap	inent Page: Grown on pl. Phys. V	s, Etc.) GaN Substra	Yes/No  actes with a 1) L1020-L1022
	OTHER DOCU  Shuji Nakamura et a Fundamental Trans	JMENTS (Includinal, "InGaN/GaN/Awerse Mode", Septe	Country  g Author, Title, Date, Pert GaN-Based Laser Diodes ember 15, 1998, Jpn. J. Ap	inent Page: Grown on pl. Phys. V	s, Etc.) GaN Substra	Yes/No  actes with a 1) L1020-L1022
OB FUND	OTHER DOCU  Shuji Nakamura et a Fundamental Trans Dan Botez "Monoli	JMENTS (Includinal, "InGaN/GaN/Awerse Mode", Septe	g Author, Title, Date, Pert GaN-Based Laser Diodes ember 15, 1998, Jpn. J. Ap Semiconductor Laser Arra	inent Page Grown on pl. Phys. V ays" Camb	class s, Etc.) GaN Substra ol. 37 (1998 ridge Univer	actes with a b) L1020-L1022 sity Press
	OTHER DOCU  Shuji Nakamura et a Fundamental Trans	JMENTS (Includinal, "InGaN/GaN/Awerse Mode", Septe	Country  g Author, Title, Date, Pert GaN-Based Laser Diodes ember 15, 1998, Jpn. J. Ap	inent Page Grown on pl. Phys. V ays" Camb	s, Etc.) GaN Substra	actes with a b) L1020-L1022 sity Press
EXAMINER:	OTHER DOCU  Shuji Nakamura et a Fundamental Trans Dan Botez "Monoli	JMENTS (Includinal, "InGaN/GaN/Awerse Mode", Septethic Phase-Locked	g Author, Title, Date, Pertigan-Based Laser Diodes ember 15, 1998, Jpn. J. Ap Semiconductor Laser Arrangement of the DATE CONSIDERED itation is in conformance via	inent Page: Grown on pl. Phys. V ays" Camb:	class s, Etc.) GaN Substra ol. 37 (1998 ridge Univer	Yes/No  actes with a 1 L1020-L1022 rsity Press